

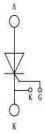
Non-isolated Thyristor Modules

Circuit configuration:3Phase Cathode Common

ITEM	V _{DRM} /V _{RRM}	I _T (AV)	I _{ISM}	I ² t	dv/dt	di/dt	I _{DRM} /I _{RRM}	I _{GT}	V _{GT}	I _H	V _{TM} /I _{TM}	V _{TO}	r _T	R _{th(j-c)}	R _{th(c-h)}	T _{jm}	Out Line No.
CONDITION	125°C	90°C	10ms		125°C		125°C		25°C		25°C	125°C		per chip			
UNIT	V	A	kA	kA ² s	V/μs	A/μs	mA	mA	V	mA	V/A	V	m·Ω	°C/W		°C	
ME100T**NK	800-1,800	100	2.5	31	800	100	8	150	2.5	120	1.67/300	0.8	2.45	0.25	0.10	125	M10
ME150T**NK	800-1,800	150	3.9	76	800	100	12	150	2.5	120	1.67/450	0.8	1.74	0.16	0.10	125	M10
ME200T**NK	800-1,800	200	5.2	135	800	100	12	150	2.5	120	1.62/600	0.8	1.15	0.13	0.10	125	M10
ME250T**NK	800-1,800	250	6.7	224	800	100	15	150	2.5	120	1.65/750	0.8	1.02	0.1	0.040	125	M11
ME300T**NK	800-1,800	300	8.3	344	800	100	15	150	2.5	120	1.58/900	0.8	0.72	0.08	0.040	125	M11

Circuit configuration:3Phase Anode Common

ITEM	V _{DRM} /V _{RRM}	I _T (AV)	I _{ISM}	I ² t	dv/dt	di/dt	I _{DRM} /I _{RRM}	I _{GT}	V _{GT}	I _H	V _{TM} /I _{TM}	V _{TO}	r _T	R _{th(j-c)}	R _{th(c-h)}	T _{jm}	Out Line No.
CONDITION	125°C	90°C	10ms		125°C		125°C		25°C		25°C	125°C		per chip			
UNIT	V	A	kA	kA ² s	V/μs	A/μs	mA	mA	V	mA	V/A	V	m·Ω	°C/W		°C	
MF100T**NA	800-1,800	100	2.5	31	800	100	8	150	2.5	120	1.67/300	0.8	2.45	0.25	0.10	125	M10
MF150T**NA	800-1,800	150	3.9	76	800	100	12	150	2.5	120	1.67/450	0.8	1.74	0.16	0.10	125	M10
MF200T**NA	800-1,800	200	5.2	135	800	100	12	150	2.5	120	1.62/600	0.8	1.15	0.13	0.10	125	M10
MF250T**NA	800-1,800	250	6.7	224	800	100	15	150	2.5	120	1.65/750	0.8	1.02	0.1	0.040	125	M11
MF300T**NA	800-1,800	300	8.3	344	800	100	15	150	2.5	120	1.58/900	0.8	0.72	0.08	0.040	125	M11



Circuit configuration:Single

ITEM	V _{DRM} /V _{RRM}	I _T (AV)	I _{ISM}	I ² t	dv/dt	di/dt	I _{DRM} /I _{RRM}	I _{GT}	V _{GT}	I _H	V _{TM} /I _{TM}	V _{TO}	r _T	R _{th(j-c)}	R _{th(c-h)}	T _{jm}	Out Line No.
CONDITION	125°C	90°C	10ms		125°C		125°C		25°C		25°C	125°C		per chip			
UNIT	V	A	kA	kA ² s	V/μs	A/μs	mA	mA	V	mA	V/A	V	m·Ω	°C/W		°C	
MH150T**NK	800-1,800	150	3.9	76	800	100	12	150	2.5	120	1.67/450	0.8	1.74	0.16	0.10	125	M09
MH200T**NK	800-1,800	200	5.2	135	800	100	12	150	2.5	120	1.62/600	0.8	1.15	0.13	0.10	125	M09
MH250T**NK	800-1,800	250	6.7	224	800	100	15	150	2.5	120	1.65/750	0.8	1.02	0.10	0.040	125	M12
MH300T**NK	800-1,800	300	8.3	344	800	100	15	150	2.5	120	1.58/900	0.8	0.72	0.08	0.040	125	M12



Circuit configuration:Single

ITEM	V _{DRM} /V _{RRM}	I _T (AV)	I _{ISM}	I ² t	dv/dt	di/dt	I _{DRM} /I _{RRM}	I _{GT}	V _{GT}	I _H	V _{TM} /I _{TM}	V _{TO}	r _T	R _{th(j-c)}	R _{th(c-h)}	T _{jm}	Out Line No.
CONDITION	125°C	90°C	10ms		125°C		125°C		25°C		25°C	125°C		per chip			
UNIT	V	A	kA	kA ² s	V/μs	A/μs	mA	mA	V	mA	V/A	V	m·Ω	°C/W		°C	
MH150T**NA	800-1,800	150	3.9	76	800	100	12	150	2.5	120	1.67/450	0.8	1.74	0.16	0.10	125	M09
MH200T**NA	800-1,800	200	5.2	135	800	100	12	150	2.5	120	1.62/600	0.8	1.15	0.13	0.10	125	M09
MH250T**NA	800-1,800	250	6.7	224	800	100	15	150	2.5	120	1.65/750	0.8	1.02	0.10	0.040	125	M12
MH300T**NA	800-1,800	300	8.3	344	800	100	15	150	2.5	120	1.58/900	0.8	0.72	0.08	0.040	125	M12